

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 02-063115

(43)Date of publication of application : 02.03.1990

(51)Int.Cl.

H01L 21/20

H01L 21/205

(21)Application number : 63-215535

(71)Applicant : NEC CORP

(22)Date of filing : 29.08.1988

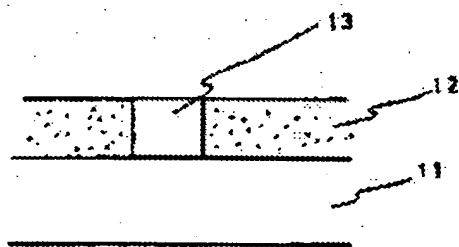
(72)Inventor : ISHIDA KOICHI

(54) SELECTIVE GROWTH OF THIN FILM

(57)Abstract:

PURPOSE: To sharply reduce a lattice defect density at the upper part of a selective epitaxial growth layer by a method wherein a thin film is grown in such a way that a ratio of a height to a width of a groove satisfies a specific condition.

CONSTITUTION: SiO₂ 12 with a film thickness of (h) is grown on a (100) Si substrate 11 by thermal oxidation; then, a square window part where a <110> direction is used as one side of a length (w) is formed in an SiO₂ mask material by a dry etching operation. Then, the substrate is installed in a low-pressure MOCVD apparatus so as to obtain $h > w \tan \theta$; the surface of Si exposed on the bottom of the window part is cleaned in AsH₃ which has been diluted by H₂; then, GaAs 13 is grown selectively in the window part in an atomic-layer growth mode by using diethyl gallium chloride (DEGaA) and AsH₃ as raw materials.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]